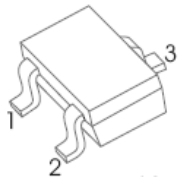
MMBT3906W

PNP Silicon Epitaxial Planar Transistor

Features

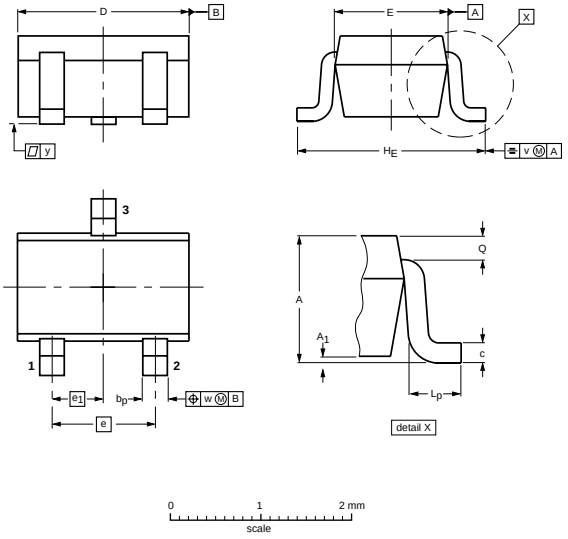
for switching and amplifier applications



SOT-323

1. BASE
2. EMITTER
3. COLLECTOR

SOT-323



DIMENSIONS (mm are the original dimensions)

UNIT	A	A_1 max	b_p	c	D	E	e	e_1	H_E	L_p	Q	v	w
mm	1.1 0.8	0.1	0.4 0.3	0.25 0.10	2.2 1.8	1.35 1.15	1.3	0.65	2.2 2.0	0.45 0.15	0.23 0.13	0.2	0.2

Absolute Maximum Ratings (T_a = 25 °C)

Parameter	Symbol	Value	Unit
Collector Base Voltage	$-V_{CBO}$	40	V
Collector Emitter Voltage	$-V_{CEO}$	40	V
Emitter Base Voltage	$-V_{EBO}$	5	V
Collector Current	$-I_C$	200	mA
Total Power Dissipation	P_{tot}	200	mW
Junction Temperature	T_j	150	°C
Storage Temperature Range	T_{stg}	- 55 to +150	°C

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Characteristics at T_a = 25 °C

Parameter	Symbol	Min.	Max.	Unit
DC Current Gain at $-V_{CE}$ = 1 V, $-I_C$ = 1 mA at $-V_{CE}$ = 1 V, $-I_C$ = 10 mA at $-V_{CE}$ = 1 V, $-I_C$ = 50 mA at $-V_{CE}$ = 1 V, $-I_C$ = 100 mA	h_{FE}	 80 100 60 30	 - 300 - -	 - - - -
Collector Emitter Cutoff Current at $-V_{CE}$ = 30 V	$-I_{CES}$	-	50	nA
Emitter Base Cutoff Current at $-V_{EB}$ = 3 V	$-I_{EBO}$	-	50	nA
Collector Base Breakdown Voltage at $-I_C$ = 10 µA	$-V_{(BR)CBO}$	40	-	V
Collector Emitter Breakdown Voltage at $-I_C$ = 1 mA	$-V_{(BR)CEO}$	40	-	V
Emitter Base Breakdown Voltage at $-I_E$ = 10 µA	$-V_{(BR)EBO}$	5	-	V
Collector Emitter Saturation Voltage at $-I_C$ = 10 mA, $-I_B$ = 1 mA at $-I_C$ = 50 mA, $-I_B$ = 5 mA	$-V_{CE(sat)}$	 - -	 0.25 0.4	V
Base Emitter Saturation Voltage at $-I_C$ = 10 mA, $-I_B$ = 1 mA at $-I_C$ = 50 mA, $-I_B$ = 5 mA	$-V_{BE(sat)}$	 0.65 -	 0.85 0.95	V
Transition Frequency at $-V_{CE}$ = 20 V, I_E = 10 mA, f = 100 MHz	f_T	250	-	MHz
Collector Output Capacitance at $-V_{CB}$ = 10 V, f = 100 KHz	C_{ob}	-	4.5	pF
Delay Time at $-V_{CC}$ = 3 V, $-V_{BE(OFF)}$ = 0.5 V, $-I_C$ = 10 mA, $-I_{B1}$ = 1 mA	t_d	-	35	ns
Rise Time at $-V_{CC}$ = 3 V, $-V_{BE(OFF)}$ = 0.5 V, $-I_C$ = 10 mA, $-I_{B1}$ = 1 mA	t_r	-	35	ns
Storage Time at $-V_{CC}$ = 3 V, $-I_C$ = 10 mA, I_{B1} = $-I_{B2}$ = -1 mA	t_{stg}	-	225	ns
Fall Time at $-V_{CC}$ = 3 V, $-I_C$ = 10 mA, I_{B1} = $-I_{B2}$ = -1 mA	t_f	-	75	ns

RATING AND CHARACTERISTIC CURVES (MMBT3906W)

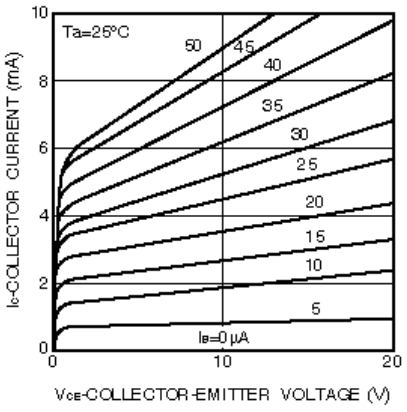

Fig.1 Grounded emitter output characteristics

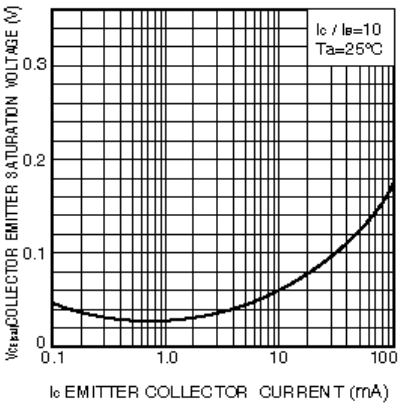

Fig.2 Collector-emitter saturation voltage vs. collector current

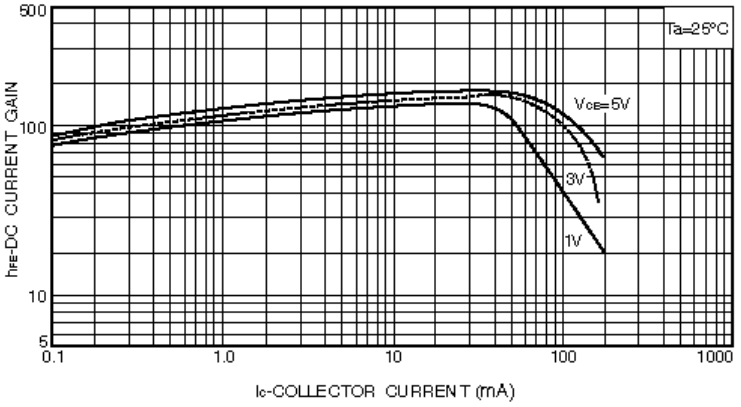

Fig.3 DC current gain vs.collector current (I)

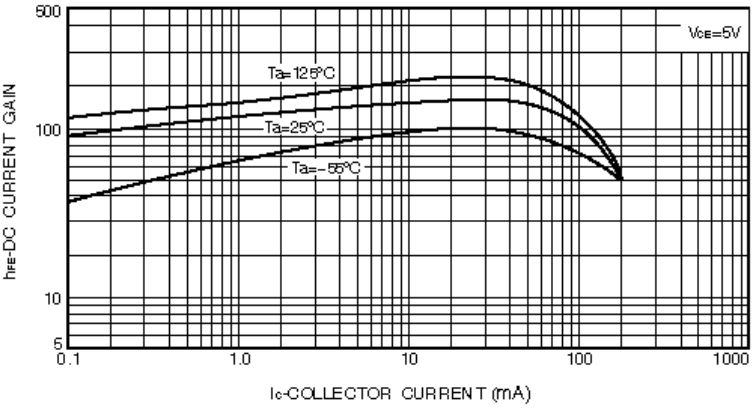

Fig.4 DC current gain vs. collector current (II)

RATING AND CHARACTERISTIC CURVES (MMBT3906W)

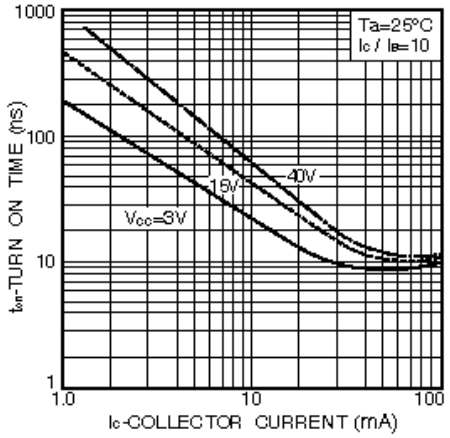

Fig.8 Turn-on time vs. collector current

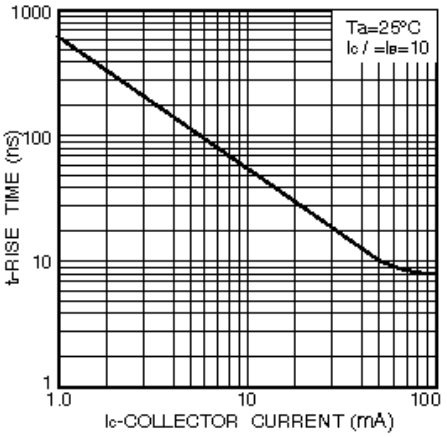

Fig.9 Rise time vs. collector current

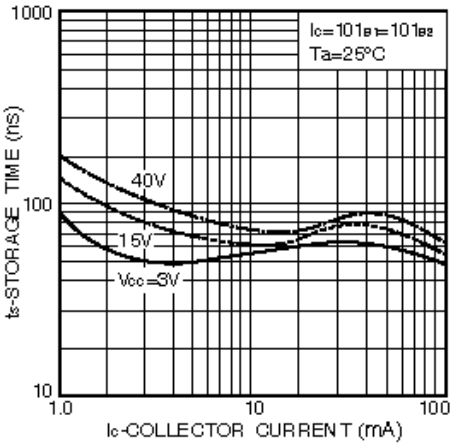

Fig.10 Storage time vs. collector current

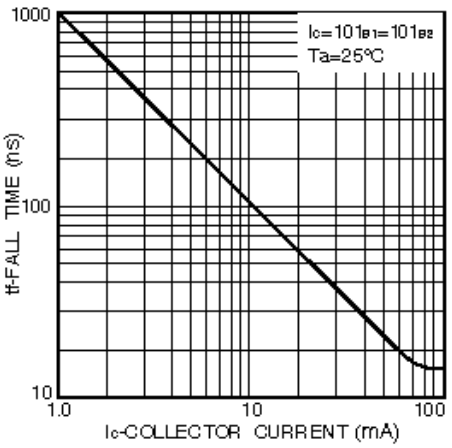

Fig.11 Fall time vs. collector current

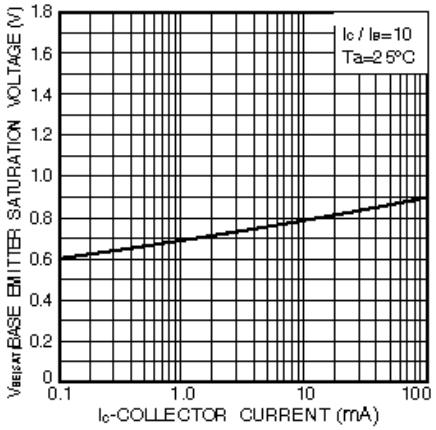

Fig.6 Base-emitter saturation voltage vs. collector current

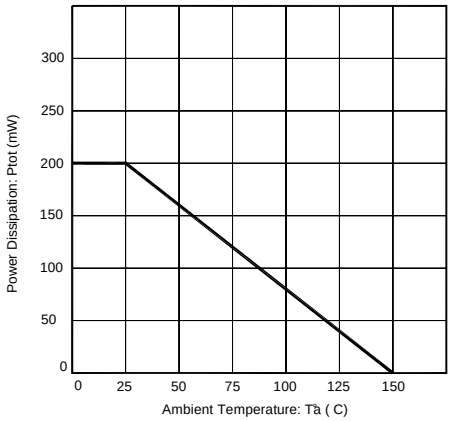

Fig.10 Power Dissipation vs Ambient Temperature

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